Product data sheet

1. General description

Hyperfast power diode in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- · Low reverse recovery current
- Low thermal resistance
- Low leakage current
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- · Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage		600			V	
I _{F(AV)}	average forward current	$δ = 0.5$; square-wave pulse; $T_{mb} \le 133$ °C; Fig. 1; Fig. 2; Fig. 3	5		А		
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 133 °C; square-wave pulse	10		А		
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4				А	
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse			А		
Symbol	Parameter	Conditions	Min Typ Max		Max	Unit	
Static ch	aracteristics						
V _F	forward voltage	I _F = 5 A; T _j = 25 °C; <u>Fig. 6</u>		-	2.5	3.3	V
		I _F = 5 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.4	2.1	V
Dynamic	characteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	11	-	ns

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BYC5-600P

Hyperfast power diode

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	
2	А	anode	7 0 5	K -
mb	mb	mounting base; connected to cathode	1 2 TO-220AC (SOD59)	001aaa020

6. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
BYC5-600P	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59	

7. Marking

Table 4. Marking codes

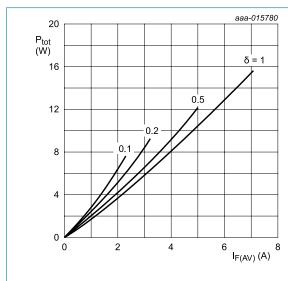
Type number	Marking codes
BYC5-600P	BYC5-600P

8. Limiting values

Table 5. Limiting values

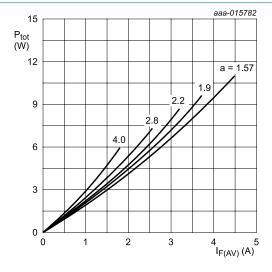
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
$I_{F(AV)}$	average forward current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 133$ °C; Fig. 1; Fig. 2; Fig. 3	5	Α
I _{FRM}	repetitive peak forward current	$δ = 0.5$; $t_p = 25 \mu s$; $T_{mb} \le 133 °C$; square-wave pulse	10	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	60	Α
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	65	А
T _{stg}	storage temperature		-65 to 175	°C
T _j	junction temperature		175	°C



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ V_o = 1.801 V; R_s = 0.062 Ω

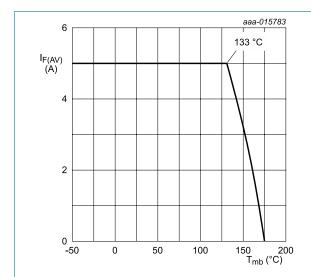
Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 1.801 V; R_s = 0.062 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

Hyperfast power diode





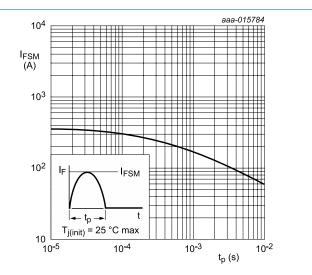


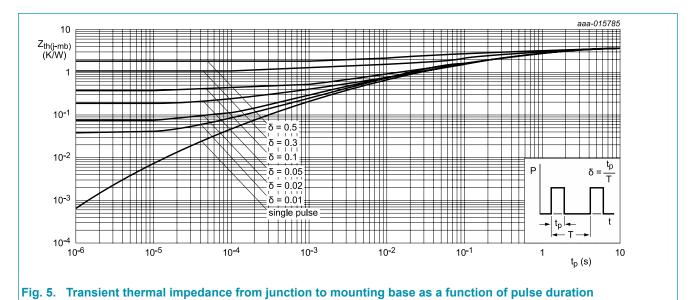
Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

Hyperfast power diode

9. Thermal characteristics

Table 6. Thermal characteristics

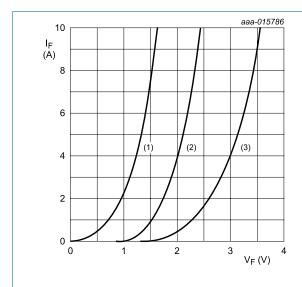
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	with heatsink compound; Fig 5	-	-	3.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W



10. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V_{F}	forward voltage	I _F = 5 A; T _j = 25 °C; <u>Fig. 6</u>	-	2.5	3.3	V
		I _F = 5 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.4	2.1	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μΑ
		V _R = 600 V; T _j = 150 °C	-	-	0.6	mA
Dynamic	characteristics			,		
Q _r	recovered charge	$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_J = 25 \text{ °C}; Fig. 7$	-	19	-	nC
		$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	45	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	11	-	ns
		$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	23	-	ns
		$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	28	-	ns
		$I_F = 5 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	13	25	ns
I _{RM}	peak reverse recovery current	$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	1.7	-	А
		$I_F = 5 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_i = 125 \text{ °C}; Fig. 7$	-	3.2	-	А

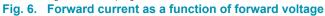


(1) $T_j = 150 \,^{\circ}\text{C}$; typical values

(2) $T_j = 150$ °C; maximum values

(3) $T_j = 25$ °C; maximum values

 $V_o = 1.801 \text{ V}; R_s = 0.062 \Omega$



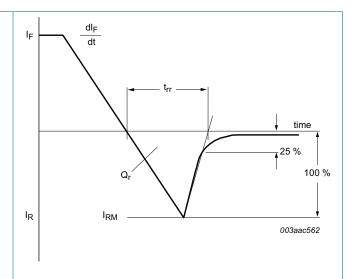
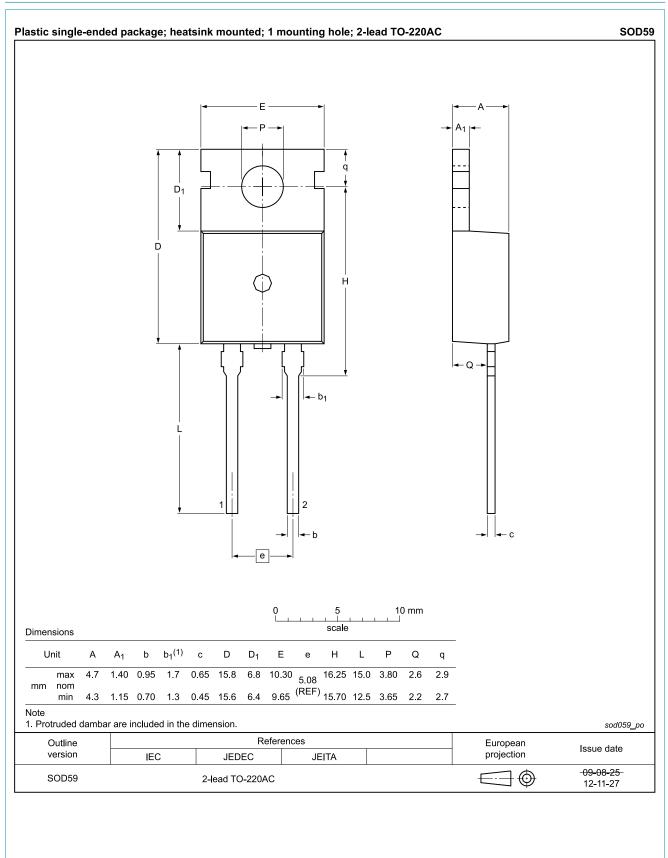


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline



Hyperfast power diode

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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Hyperfast power diode

13. Contents

1. General description	1
2. Features and benefits	1
3. Applications	1
4. Quick reference data	1
5. Pinning information	2
6. Ordering information	2
7. Marking	2
8. Limiting values	3
9. Thermal characteristics	5
10. Characteristics	6
11. Package outline	7
12. Legal information	
13. Contents	

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Date of release: 1 March 2018

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